

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

1. (Currently amended) A semiconductor device comprising:

a base substrate provided with a base wiring;

a first substrate that extends from a first side of the base substrate to a second side of the base substrate and includes a first wiring to be electrically connected to the base wiring on both the first and second sides of the base substrate, and wherein the first substrate is provided above the base substrate;

a first semiconductor element that is provided between the base substrate and the first substrate;

a second substrate that extends from a third side of the base substrate to a fourth side of the base substrate and includes a second wiring to be electrically connected to the base wiring on both the third and fourth sides of the base substrate, and wherein the second substrate is provided above the first substrate; and

a second semiconductor element that is provided between the first substrate and the second substrate and above the first semiconductor element,

wherein the first substrate has a first region where the first semiconductor element is provided below, [[a]] second regions where [[a]] portions of the first wiring that connects to the base wiring [[is]] are located, and [[a]] first bent sections between the first region and the second regions, and

the second substrate has a third region where the second semiconductor element is provided below, [[a]] fourth regions where [[a]] portions of the second wiring that connects to the base wiring [[is]] are located, and [[a]] second bent sections between the third region and the fourth regions.

2. (Original) The semiconductor device according to claim 1, further comprising:

a first electrode that is provided on the first semiconductor element; and
a second electrode that is provided on the second semiconductor element,
wherein the first electrode is electrically connected to the first wiring, and
the second electrode is electrically connected to the second wiring.

3. (Original) The semiconductor device according to claim 2, further comprising:

a surface of the first semiconductor element that includes the first electrode
has a rectangular shape including a first side and a second side that is longer than
the first side and intersects the first side; and

a surface of the second semiconductor element that includes the second electrode
has a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side,

wherein the first semiconductor element and the second semiconductor
element are disposed such that the second side and the fourth side are in parallel
with each other.

4. (Original) The semiconductor device according to claim 2, further comprising:

a surface of the first semiconductor element that includes the first electrode
has a rectangular shape including a first side and a second side that is longer than
the first side and intersects the first side; and

a surface of the second semiconductor element that includes the second electrode
has a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side,

wherein the first semiconductor element and the second semiconductor
element are disposed such that the second side and the fourth side projected onto
the base substrate intersect each other.

5. (Canceled).

6. (Currently amended) The semiconductor device according to claim 1, further comprising:

a surface of the first substrate that opposes a surface of the base substrate has, when viewed from above, a rectangular shape including a first side and a second side that is longer than the first side and intersects the first side; and

a surface of the second substrate that opposes a surface of the base substrate has, when viewed from above, a rectangular shape including a third side and a fourth side that is longer than the third side and intersects the third side,

wherein the first substrate and the second substrate are disposed such that the second side and the fourth side projected onto the base substrate intersect each other.

7. (Currently amended) The semiconductor device according to claim 1, wherein ~~an~~ opening sections ~~is~~ are formed in the first substrate at the first bent sections.

8. (Currently amended) The semiconductor device according to claim 1, wherein ~~an~~ opening sections ~~is~~ are formed in the second substrate at the second bent sections.

9-22. (Canceled)